

Patent Application
10/010,162

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Iwu-Iuan Hshieh et al.
Serial No.: 10/010,162
Filed: November 20, 2001
Title: Method Of Forming Narrow Trenches In Semiconductor Substrates
Art Unit: 2812
Examiner: Angel Roman
Docket No.: GS 149
Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

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**PETITION UNDER 37 CFR 1.136(a), AMENDMENT and
SUBMISSION OF FORMAL DRAWINGS**

Applicants hereby petition the Assistant Commissioner to grant a two month extension of time, up to and including November 24, 2004, in which to respond to the Office Action dated June 24, 2004 in the above-identified application. The additional extension fee in the amount of \$420.00 may be charged to deposit account No. 50-1047. In addition, any deficiencies may be charged to deposit account No. 50-1047.

In response to the Office Action dated June 24, 2004, the period therefore having been extended by a Petition therefore and payment of the extension fee, kindly amend the above-identified application as follows.

Certificate of Facsimile Transmission

I hereby certify that this document and any document referenced herein has been transmitted via facsimile to the U.S. Patent and Trademark Office at (703) 872-9318 on November 21, 2004.

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